



PHPT61002NYC

100V, 2 A NPN high power bipolar transistor

9 January 2014

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61002PYC

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation

3. Applications

- Load switch
- Power management
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
I_C	collector current		-	-	2	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	6	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 2$ A; $I_B = 200$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C	-	80	150	m Ω

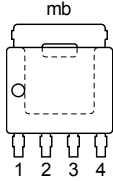
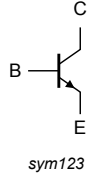


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LFPAK56; Power-SO8 (SOT669)</p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61002NYC	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61002NYC	1002NCA

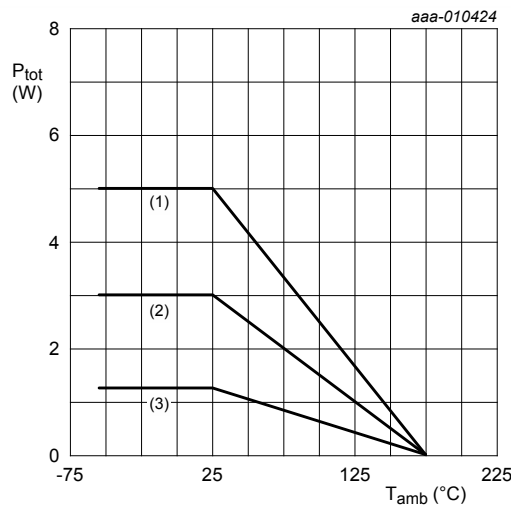
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	6	A
I _B	base current			-	0.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

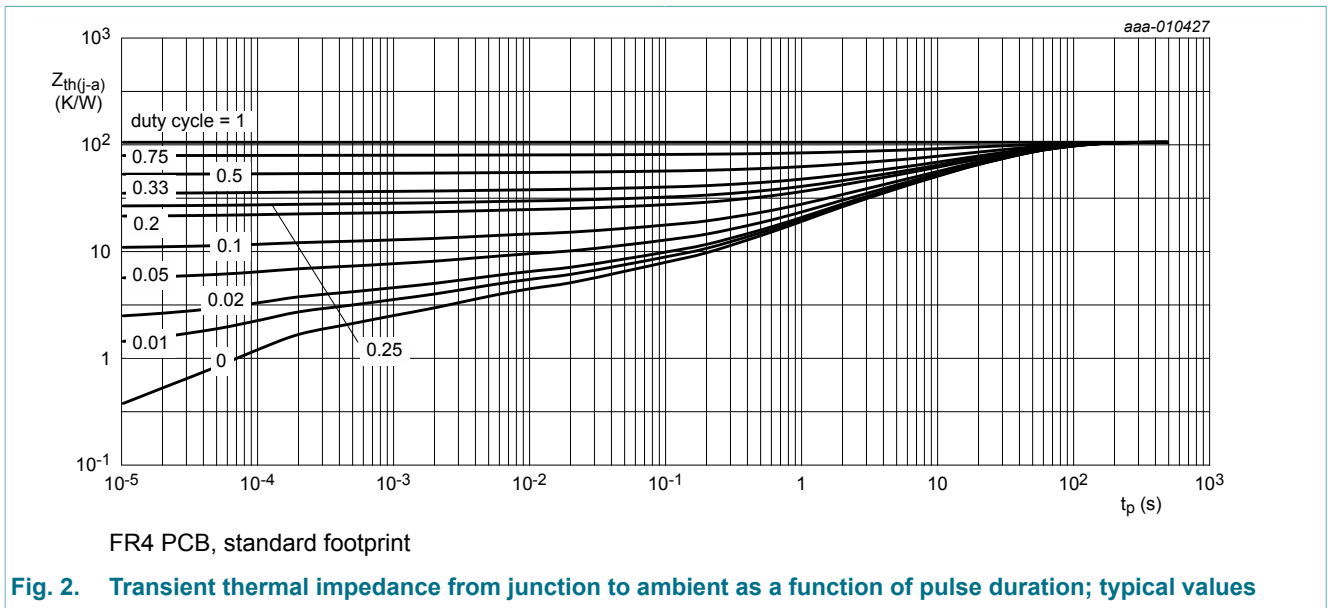
Fig. 1. Power derating curves

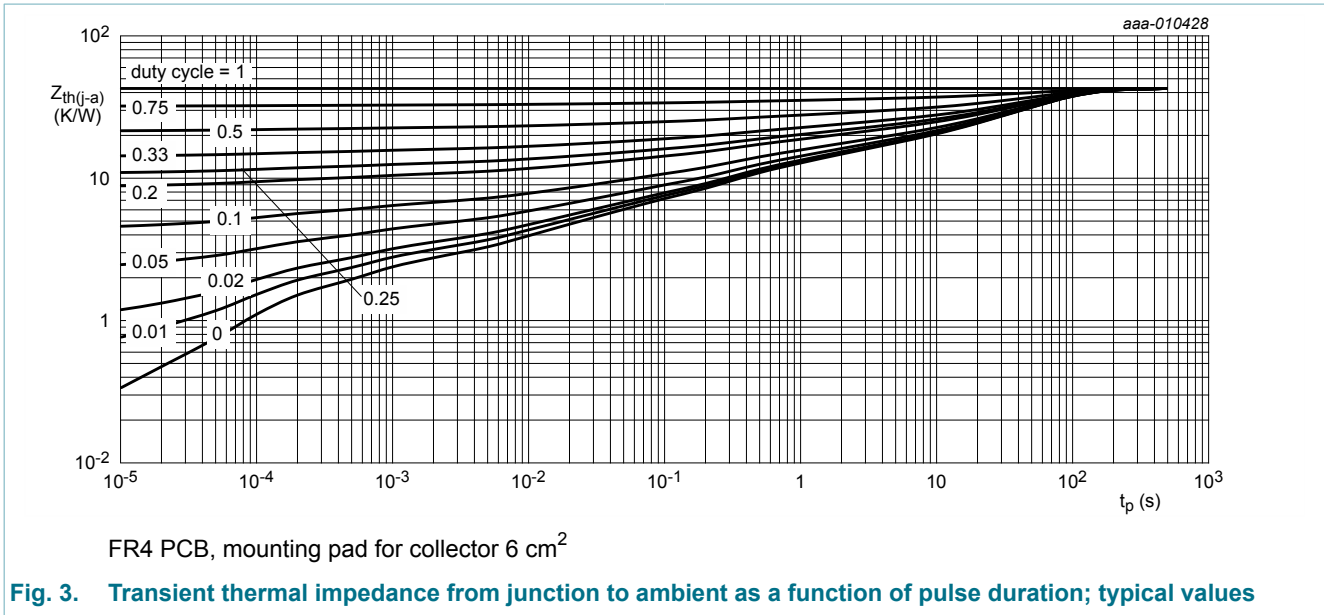
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB, Al₂O₃, standard footprint.

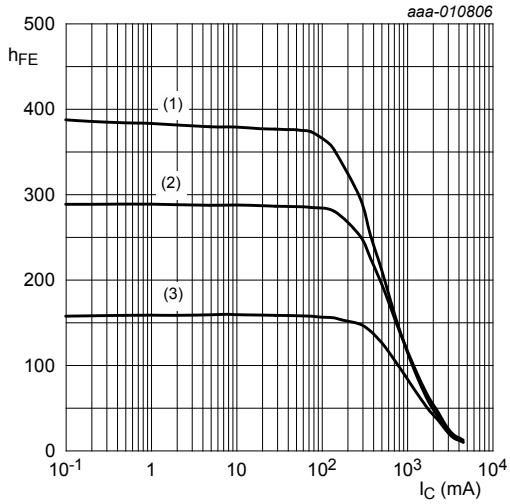




10. Characteristics

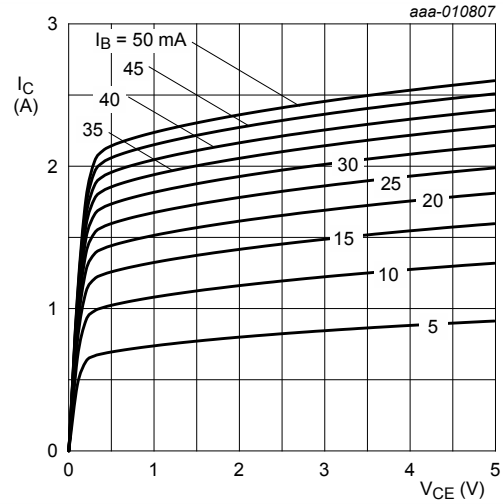
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
		V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 1.5 V; I _C = 500 mA; T _{amb} = 25 °C	100	200	-	
		V _{CE} = 10 V; I _C = 500 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	150	250	-	
		V _{CE} = 10 V; I _C = 1 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	80	200	-	
		V _{CE} = 10 V; I _C = 2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	20	140	-	
		V _{CE} = 10 V; I _C = 3 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	10	100	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 50 mA; T _{amb} = 25 °C	-	50	75	mV
		I _C = 2 A; I _B = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	160	300	mV
R _{CEsat}	collector-emitter saturation resistance	t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	80	150	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.92	1	V
		I _C = 2 A; I _B = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	1.08	1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 0.1 A; T _{amb} = 25 °C	-	0.68	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A; I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	20	-	ns
t _r	rise time		-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns
f _T	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF



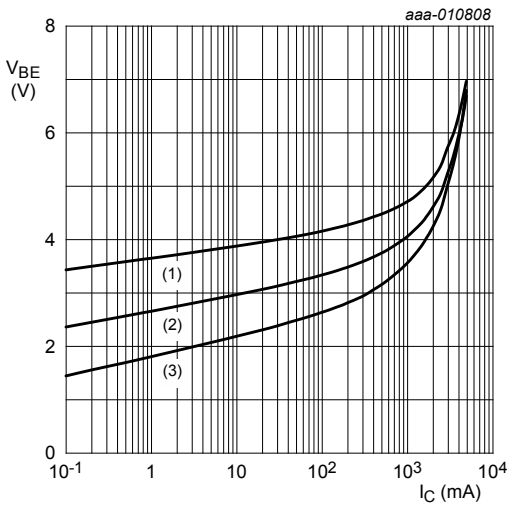
$V_{CE} = 1\text{ V}$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig. 4. DC current gain as a function of collector current; typical values



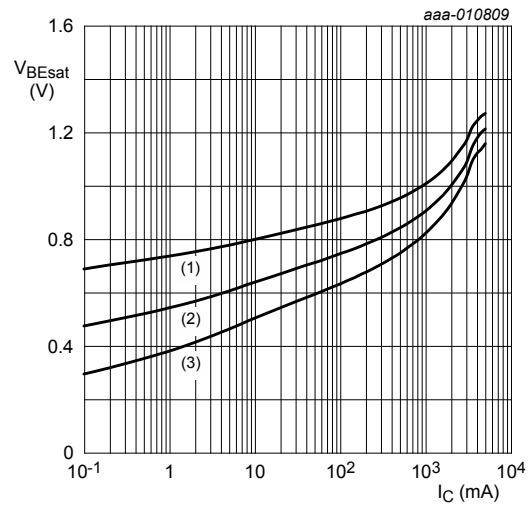
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig. 5. Collector current as a function of collector-emitter voltage; typical values



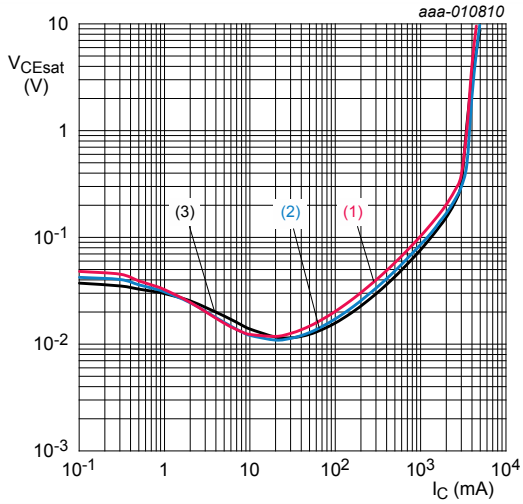
$V_{CE} = 2\text{ V}$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



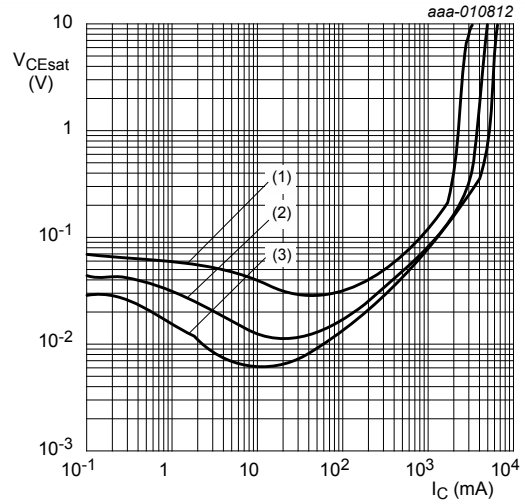
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



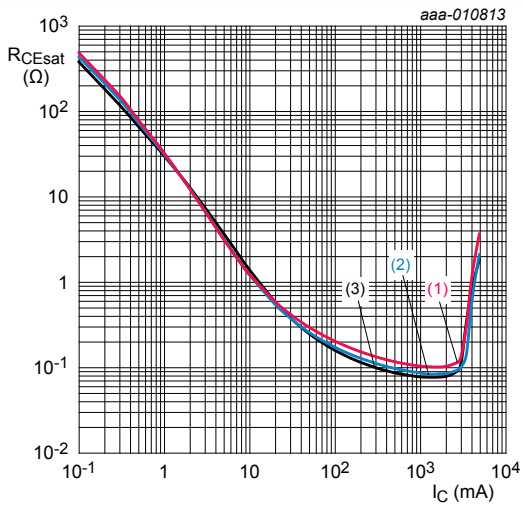
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



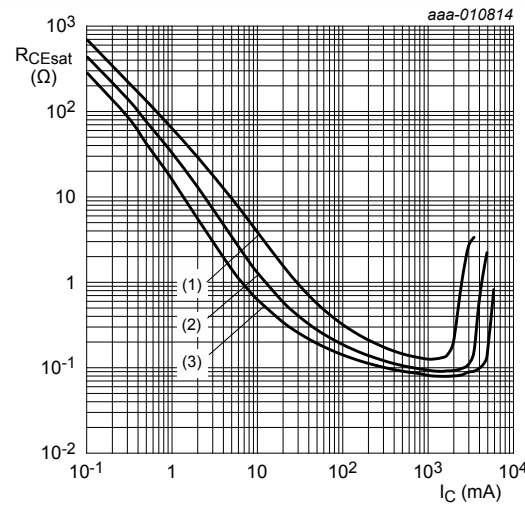
$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

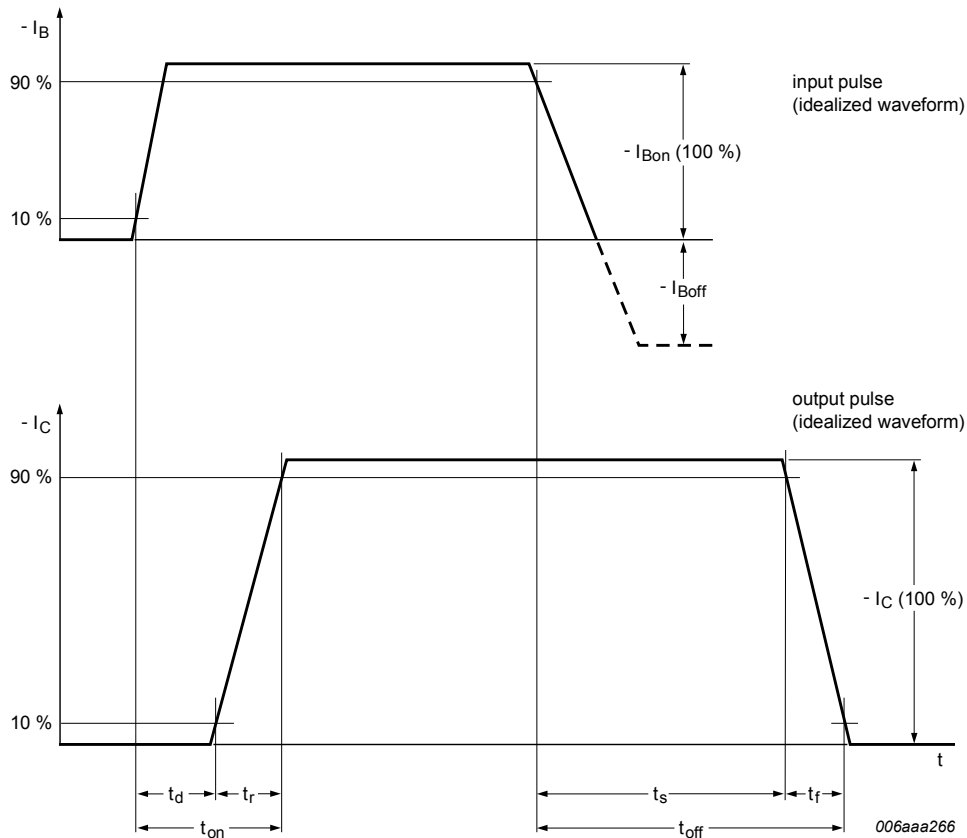


Fig. 12. BISS transistor switching time definition

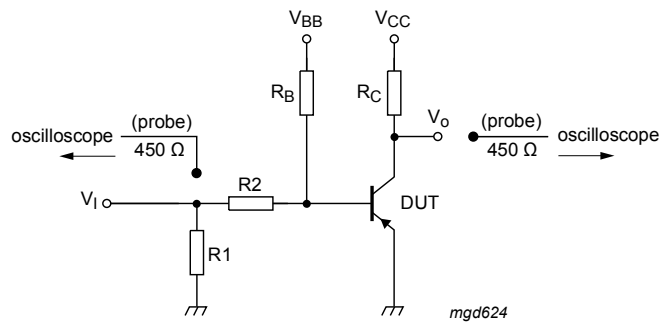
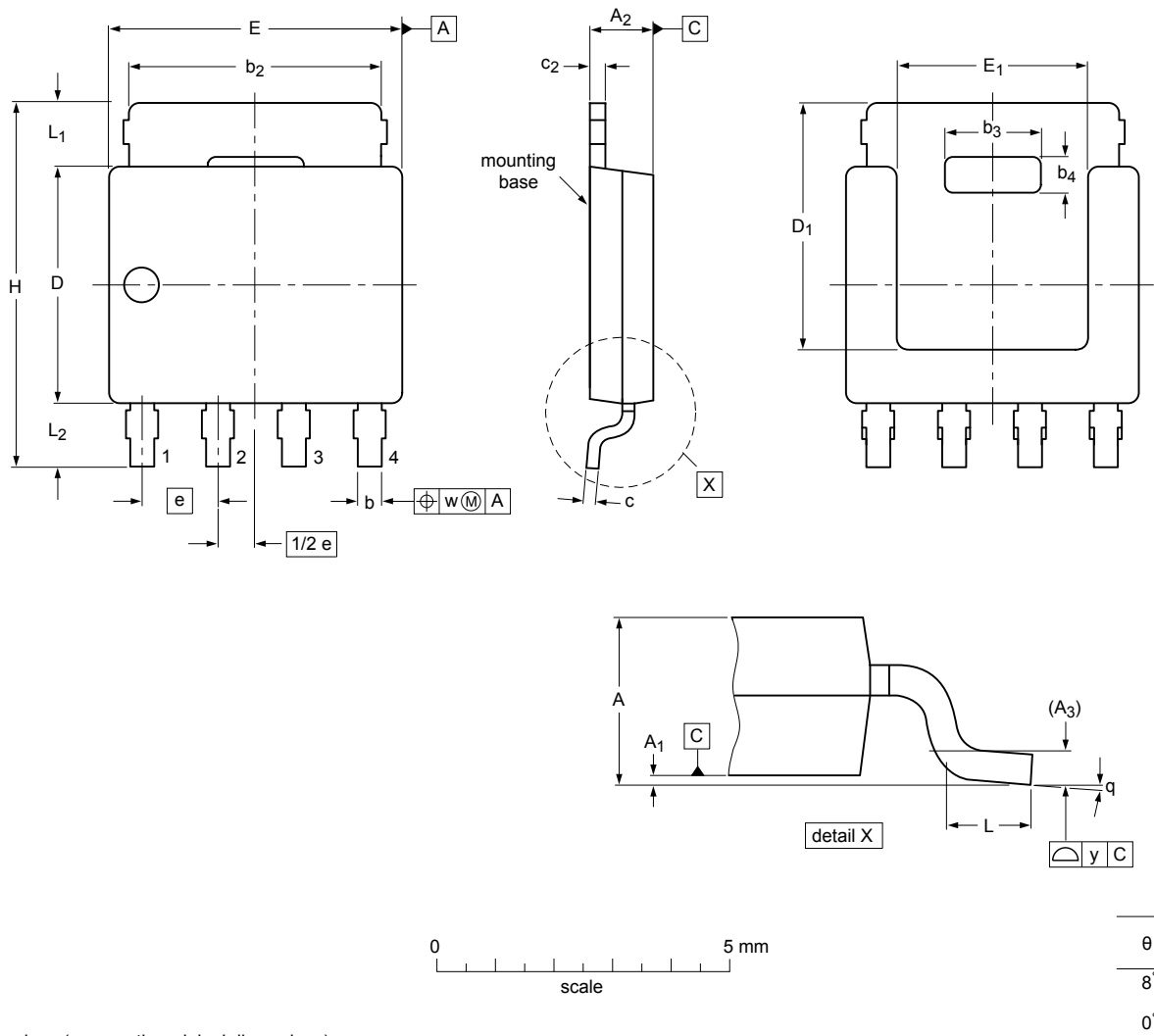


Fig. 13. Test circuit for switching times

12. Package outline

Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads SOT669



Dimensions (mm are the original dimensions)

Unit ⁽¹⁾	A	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	c	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾	E ⁽¹⁾	E ₁ ⁽¹⁾	e	H	L	L ₁	L ₂	w	y
max	1.20	0.15	1.10		0.50	4.41	2.2	0.9	0.25	0.30	4.10	4.20	5.0	3.3		6.2	0.85	1.3	1.3		
nom				0.25											1.27					0.25	0.1
min	1.01	0.00	0.95		0.35	3.62	2.0	0.7	0.19	0.24	3.80		4.8	3.1		5.8	0.40	0.8	0.8		

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT669		MO-235				-11-03-25- 13-02-27

Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

13. Soldering

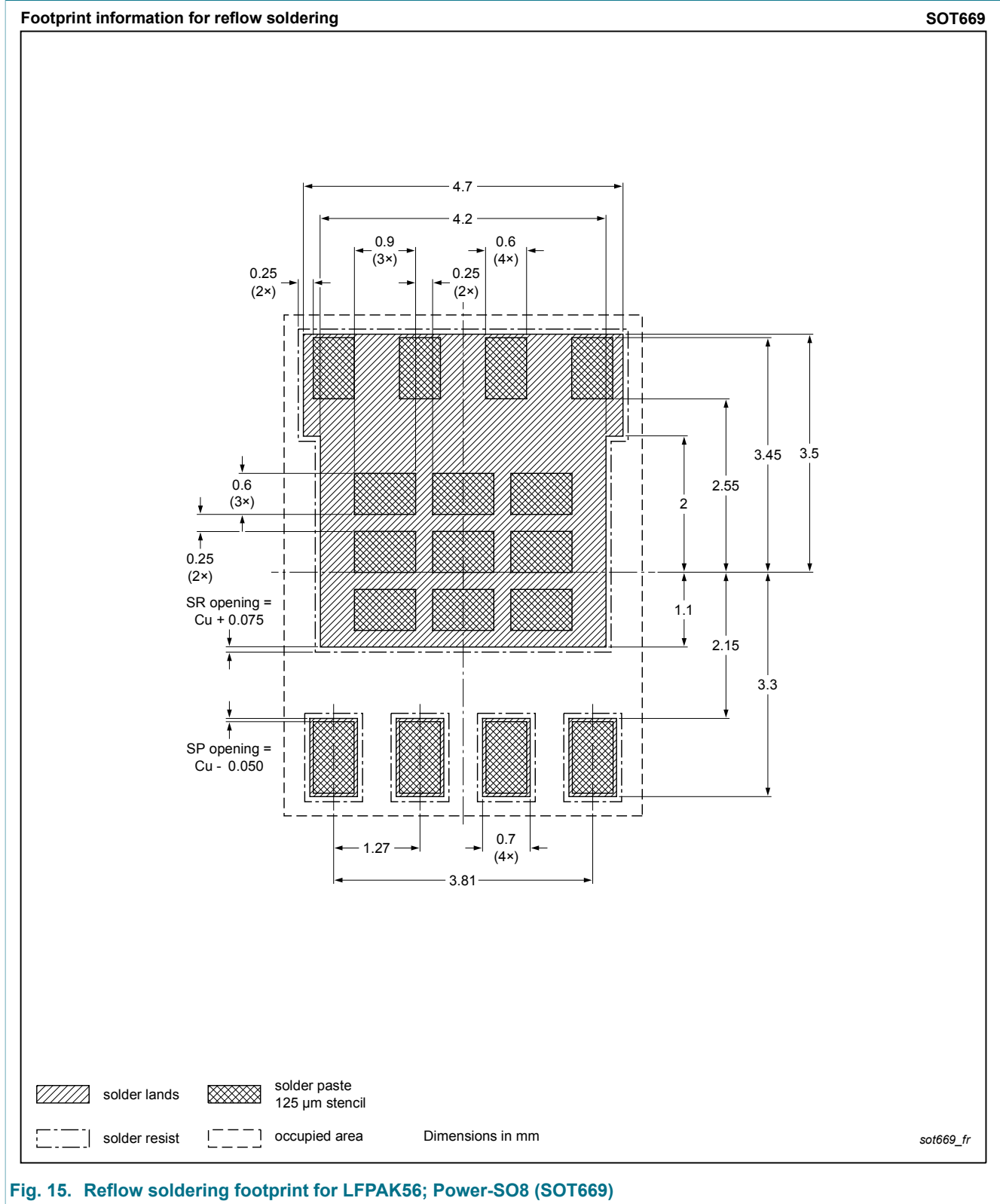


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61002NYC v.1	20140109	Product data sheet	-	-

15. Legal information

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Document status [1][2]	Product status [3]	Definition
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Date of release: 9 January 2014

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